

32000 U.S. PTO  
09/904129

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Class	Subclass	ISSUE CLASSIFICATION
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PATENT NUMBER
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U.S. UTILITY Patent Application

O.I.P.E.	PATENT DATE
AK SCANNED TKI Q.A. GW	

APPLICATION NO. 09/904129	CONT/PRIOR	CLASS 428 117	SUBCLASS 698 84	ART UNIT 1775 1765	EXAMINER STEIN
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APPLICANTS

Tetsuzo Ueda

SONG

Buffer layer and growth method for subsequent epitaxial growth of  
InAlV nitride semiconductors

PTO-2040  
12/99

ISSUING CLASSIFICATION

ORIGINAL		CROSS REFERENCE(S)			
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)		
INTERNATIONAL CLASSIFICATION					

☐ Continued on Issue Slip Inside File Jacket

<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>	<b>DRAWINGS</b>			<b>CLAIMS ALLOWED</b>	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	(Assistant Examiner) _____ (Date) _____			<b>NOTICE OF ALLOWANCE MAILED</b>	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S. Patent. No. _____					
<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.	(Primary Examiner) _____ (Date) _____			<b>ISSUE FEE</b>	
				Amount Due	Date Paid
	(Legal Instruments Examiner) _____ (Date) _____			<b>ISSUE BATCH NUMBER</b>	

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